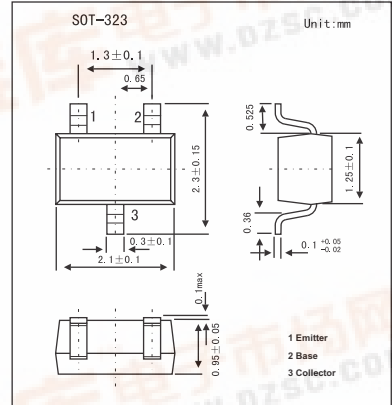


SMD Type Transistors

PNP Silicon Epitaxia
2SA1611

■ Features

- High DC Current Gain.
- High Voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-100	mA
Total power dissipation	P _T	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -60V, I _E =0			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μA
DC current gain *	h _{FE}	V _{CE} = -6V, I _C = -1mA	90	200	600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA		-0.18	-0.3	V
Base-emitter voltage	V _{BE}	V _{CE} = -6V, I _C = 1mA	-0.58	-0.62	-0.68	V
Gain bandwidth product	f _T	V _{CE} = -6V, I _E = 10mA		180		MHz
Output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1.0MHz		4.5		pF

* Pulse test: t_p ≤ 300 μs; d ≤ 0.02.

■ hFE Classification

Marking	M4	M5	M6	M7
hFE	90~180	135~270	200~400	300~600

